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N-Channel 40 V (D-S) MOSFET

PRODUCT SUMMARY						
V _{DS} (V)	R _{DS(on)} (Ω) MAX.	I _D (A) ^d	Q _g (TYP.)			
40	0.0016 at V _{GS} = 10 V	300	250			
40	0.0019 at $V_{GS} = 7.5 \text{ V}$	250	230			

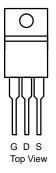
FEATURES

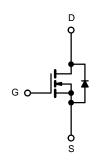
- DT-Trench Power MOSFET
- Maximum 175 °C junction temperature



- Q_{gd}/Q_{gs} ratio < 0.5
- Operable with logic-level gate drive
- 100 % R_g and UIS tested

TO-220AB





N-Channel MOSFET

APPLICATIONS

- Power supply
 - Secondary synchronous rectification
- DC/DC converter
- Power tools
- Motor drive switch
- DC/AC inverter
- Battery management

PARAMETER	SYMBOL	LIMIT	UNIT	
Drain-Source Voltage	V _{DS}	40	.,	
Gate-Source Voltage	V _{GS}	± 20	V	
Continuous Drain Current /T 150 °C	T _C = 25 °C		300 ^d	
Continuous Drain Current (T _J = 150 °C)	T _C = 70 °C	l _D	240 ^d	٦ ,
Pulsed Drain Current (t = 100 μs)	I _{DM}	1200	_ A	
Avalanche Current	L = 0.1 mH	I _{AS}	290	
Single Avalanche Energy ^a	T L= U.1 MH	E _{AS}	1550	mJ
Manianum Danum Dissipation 8	T _C = 25 °C	D .	396 b	14/
Maximum Power Dissipation ^a	T _C = 125 °C	P _D	125 ^b	W
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to +175	°C

THERMAL RESISTANCE RATINGS						
PARAMETER	SYMBOL	LIMIT	UNIT			
Junction-to-Ambient (PCB Mount) ^c	R _{thJA}	39	°C/W			
Junction-to-Case (Drain)	R _{thJC}	0.4				

Notes

- a. Duty cycle $\leq 1 \%$.
- b. See SOA curve for voltage derating.
- c. When mounted on 1" square PCB (FR4 material).
- d. Package limited.



PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static							
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA	40	-	-	V	
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \mu A$	1.0	-	3.0	v	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$	-	-	± 250	nA	
		V _{DS} = 40 V, V _{GS} = 0 V	-	-	1	μΑ	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 40 V, V _{GS} = 0 V, T _J = 125 °C	-	-	150		
-		V _{DS} = 40 V, V _{GS} = 0 V, T _J = 175 °C	-	-	5	mA	
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≥ 10 V, V _{GS} = 10 V	300	-	-	Α	
Drain-Source On-State Resistance ^a	_	V _{GS} = 10 V, I _D = 30 A	-	0.0016	0.0018	Ω	
	R _{DS(on)}	$V_{GS} = 7.5 \text{ V}, I_D = 20 \text{ A}$	-	0.0019	0.0021		
Forward Transconductance ^a	9 _{fs}	$V_{DS} = 15 \text{ V}, I_D = 30 \text{ A}$	-	175	-	S	
Dynamic ^b							
Input Capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = 30 V, f = 1 MHz	-	12100	-	pF	
Output Capacitance	Coss		-	2410	-		
Reverse Transfer Capacitance	C _{rss}		-	890	-		
Total Gate Charge c	Q_g		-	250	-	nC	
Gate-Source Charge ^c	Q _{gs}	$V_{DS} = 20 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 20 \text{ A}$	-	32	-		
Gate-Drain Charge ^c	Q _{gd}		-	11	-		
Gate Resistance	R_g	f = 1 MHz	0.32	1.6	3.2	Ω	
Turn-On Delay Time ^c	t _{d(on)}		-	14	-	ns	
Rise Time ^c	t _r	$V_{DD} = 20 \text{ V, } R_L = 5 \Omega$ $I_D \cong 10 \text{ A, } V_{GEN} = 10 \text{ V, } R_g = 1 \Omega$	-	25	-		
Turn-Off Delay Time c	t _{d(off)}		-	60	-		
Fall Time ^c	t _f		-	19	-		
Drain-Source Body Diode Ratings ar	nd Characteris	stics ^b (T _C = 25 °C)					
Pulsed Current (t = 100 μs)	I _{SM}		-	-	1200	Α	
Forward Voltage ^a	V_{SD}	I _F = 10 A, V _{GS} = 0 V	-	0.7	1.2	٧	
Reverse Recovery Time	t _{rr}		-	133	-	ns	
Peak Reverse Recovery Charge	I _{RM(REC)}	$I_F = 41 \text{ A}, \text{ di/dt} = 100 \text{ A/}\mu\text{s}$	-	9	-	Α	
Reverse Recovery Charge	Q _{rr}		-	0.32	_	иC	

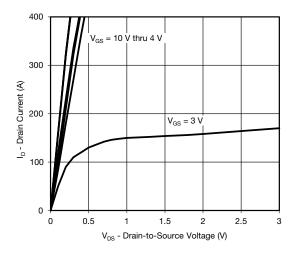
Notes

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

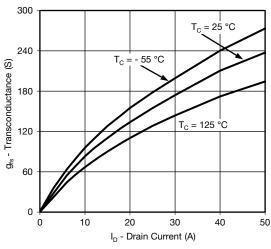
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



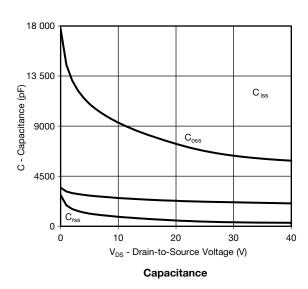
TYPICAL CHARACTERISTICS ($T_A = 25$ °C, unless otherwise noted)

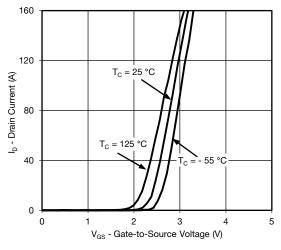


Output Characteristics

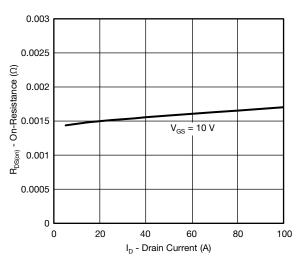


Transconductance

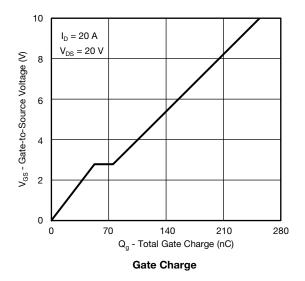




Transfer Characteristics

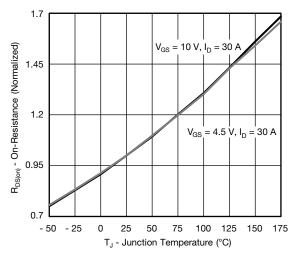


On-Resistance vs. Drain Current

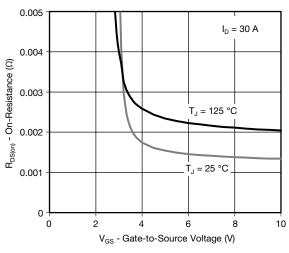




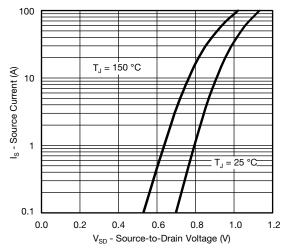
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



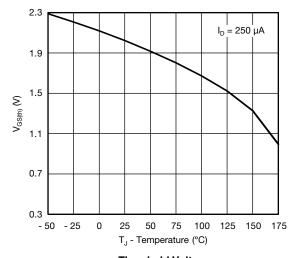
On-Resistance vs. Junction Temperature



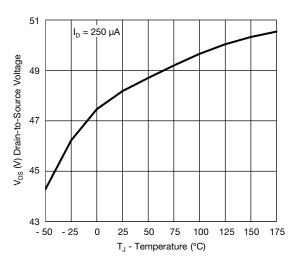
On-Resistance vs. Gate-to-Source Voltage



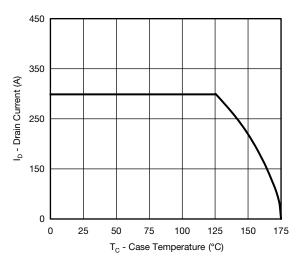
Source Drain Diode Forward Voltage



Threshold Voltage



Drain Source Breakdown vs. Junction Temperature

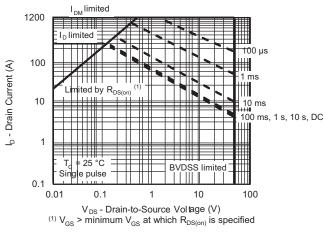


Current De-rating

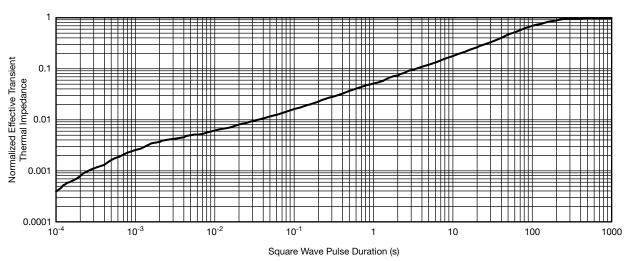




THERMAL RATINGS ($T_A = 25$ °C, unless otherwise noted)



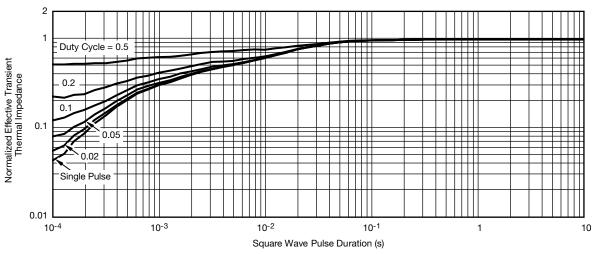
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

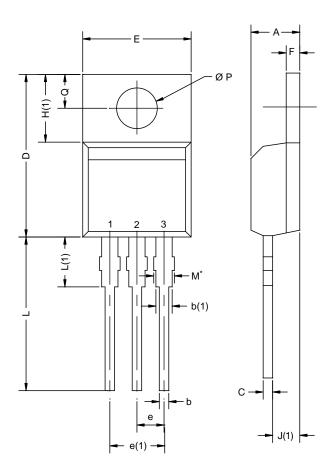
Note

- The characteristics shown in the two graphs
- Normalized Transient Thermal Impedance Junction to Ambient (25 °C)
- Normalized Transient Thermal Impedance Junction to Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.



TO-220AB



	MILLIMETERS		INC	HES	
DIM.	MIN.	MAX.	MIN.	MAX.	
Α	4.25	4.65	0.167	0.183	
b	0.69	1.01	0.027	0.040	
b(1)	1.20	1.73	0.047	0.068	
С	0.36	0.61	0.014	0.024	
D	14.85	15.49	0.585	0.610	
Е	10.04	10.51	0.395	0.414	
е	2.41	2.67	0.095	0.105	
e(1)	4.88	5.28	0.192	0.208	
F	1.14	1.40	0.045	0.055	
H(1)	6.09	6.48	0.240	0.255	
J(1)	2.41	2.92	0.095	0.115	
L	13.35	14.02	0.526	0.552	
L(1)	3.32	3.82	0.131	0.150	
ØΡ	3.54	3.94	0.139	0.155	
Q	2.60	3.00	0.102	0.118	
ECN: X12-0208-Rev. N, 08-Oct-12 DWG: 5471					

Notes

 $^{^{*}}$ M = 1.32 mm to 1.62 mm (dimension including protrusion) Heatsink hole for HVM





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